

Article

Volatile Resistive Switching Characteristics of Pt/HfO₂/TaO_x/TiN Short-Term Memory Device

Hojeong Ryu and Sungjun Kim*

Division of Electronics and Electrical Engineering, Dongguk University, Seoul 04620, South Korea; hojeong.ryu95@gmail.com

* Correspondence: sungjun@dongguk.edu

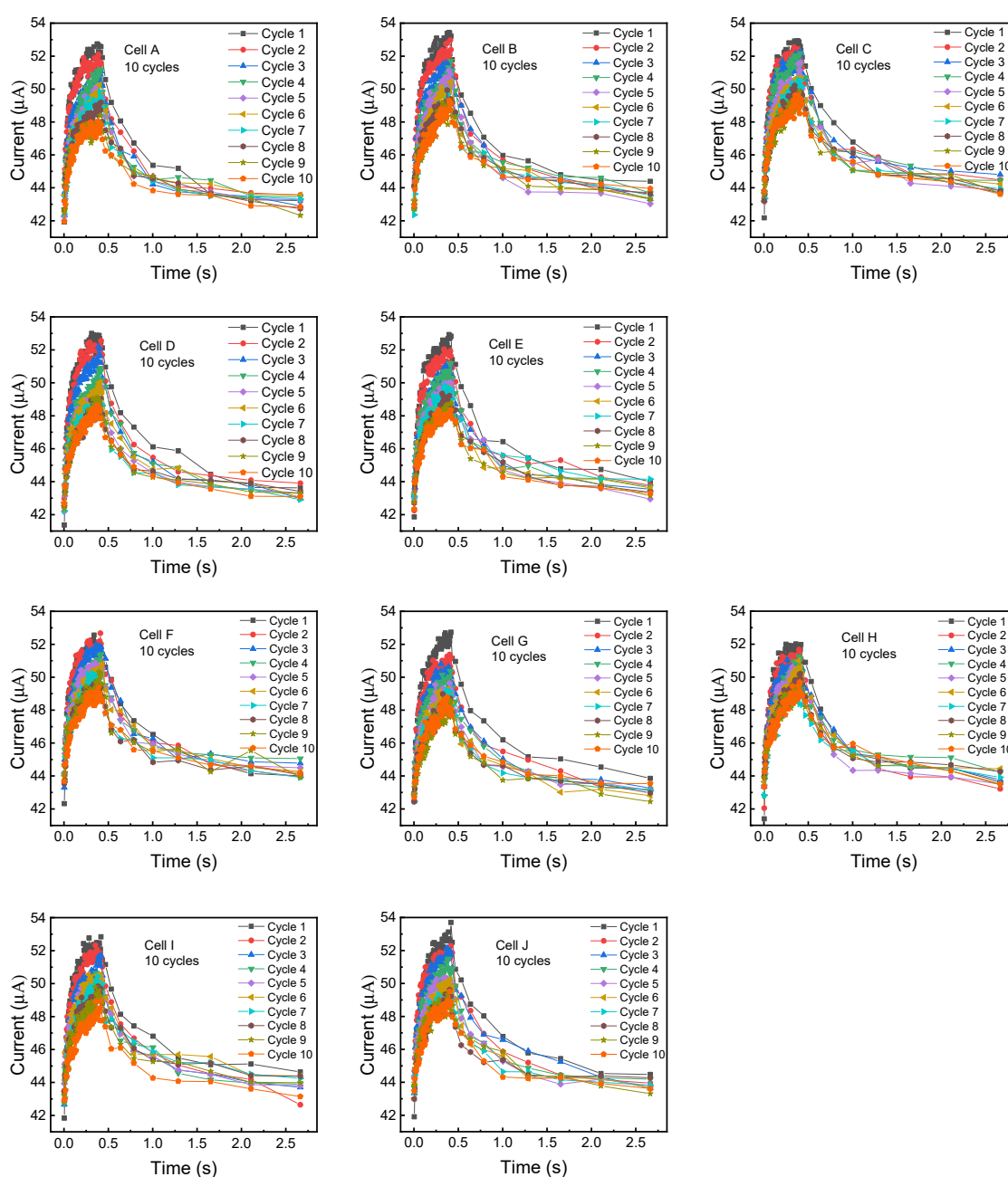


Figure S1. 10 cycles of 10 cells for current decay.

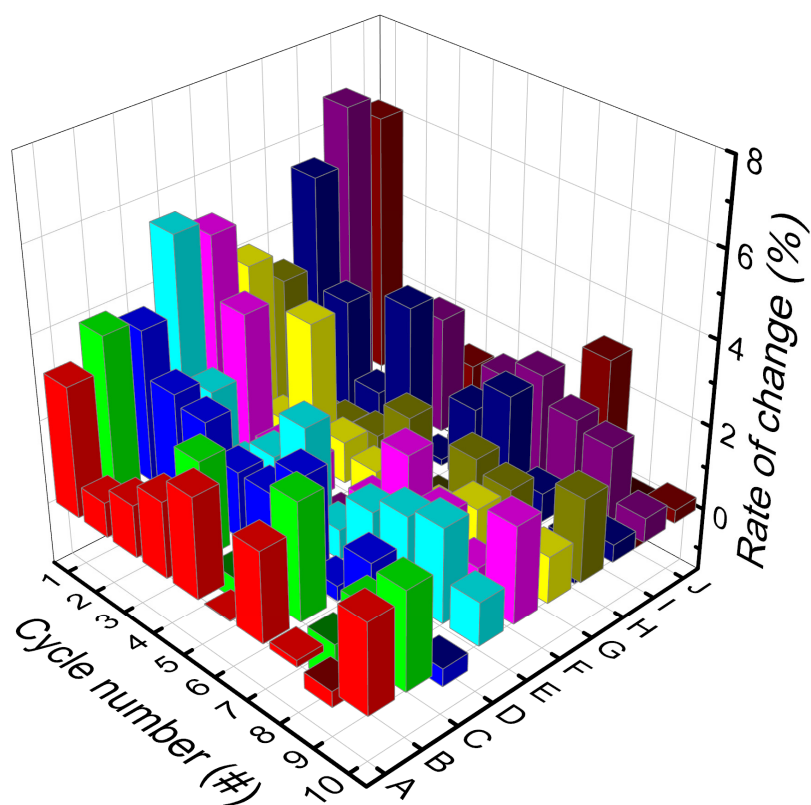


Figure S2. Change of rate for 10 cycles of 10 cells.